

LMP91000 Sensor AFE System: Configurable AFE Potentiostat for Low-Power Chemical Sensing Applications

Check for Samples: [LMP91000](#)

FEATURES

- Typical Values, $T_A = 25^\circ\text{C}$
- Supply Voltage 2.7 V to 5.25 V
- Supply Current (Average Over Time) $<10\ \mu\text{A}$
- Cell Conditioning Current up to 10 mA
- Reference Electrode Bias Current (85°C) 900pA (max)
- Output Drive Current 750 μA
- Complete Potentiostat Circuit to Interface to Most Chemical Cells
- Programmable Cell Bias Voltage
- Low Bias Voltage Drift
- Programmable TIA gain 2.75k Ω to 350k Ω
- Sink and Source Capability
- I²C Compatible Digital Interface
- Ambient Operating Temperature -40°C to 85°C
- Package 14 pin WSON
- Supported by WEBENCH[®] Sensor AFE Designer

APPLICATIONS

- Chemical Species Identification
- Amperometric Applications
- Electrochemical Blood Glucose Meter

DESCRIPTION

The LMP91000 is a programmable Analog Front End (AFE) for use in micro-power electrochemical sensing applications. It provides a complete signal path solution between a sensor and a microcontroller that generates an output voltage proportional to the cell current. The LMP91000's programmability enables it to support multiple electrochemical sensors such as 3-lead toxic gas sensors and 2-lead galvanic cell sensors with a single design as opposed to the multiple discrete solutions. The LMP91000 supports gas sensitivities over a range of 0.5 nA/ppm to 9500 nA/ppm. It also allows for an easy conversion of current ranges from 5 μA to 750 μA full scale.

The LMP91000's adjustable cell bias and transimpedance amplifier (TIA) gain are programmable through the I²C interface. The I²C interface can also be used for sensor diagnostics. An integrated temperature sensor can be read by the user through the VOUT pin and used to provide additional signal correction in the μC or monitored to verify temperature conditions at the sensor.

The LMP91000 is optimized for micro-power applications and operates over a voltage range of 2.7V to 5.25V. The total current consumption can be less than 10 μA . Further power savings are possible by switching off the TIA amplifier and shorting the reference electrode to the working electrode with an internal switch.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

WEBENCH is a registered trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

Typical Application

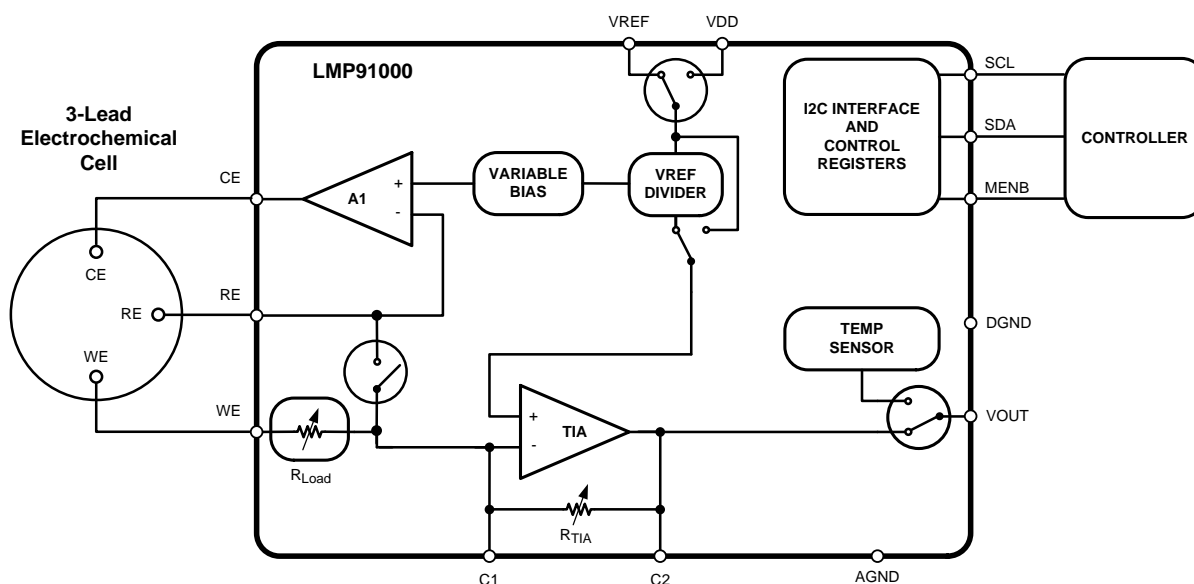


Figure 1. AFE Gas Detector

Connection Diagram

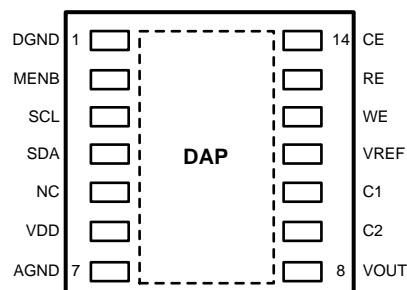


Figure 2. 14-Pin WSON — Top View

Pin Descriptions

Name	Pin	Description
DGND	1	Connect to ground
MENB	2	Module Enable, Active Low
SCL	3	Clock signal for I ² C compatible interface
SDA	4	Data for I ² C compatible interface
NC	5	Not Internally Connected
VDD	6	Supply Voltage
AGND	7	Ground
VOUT	8	Analog Output
C2	9	External filter connector (Filter between C1 and C2)
C1	10	External filter connector (Filter between C1 and C2)
VREF	11	Voltage Reference input
WE	12	Working Electrode. Output to drive the Working Electrode of the chemical sensor
RE	13	Reference Electrode. Input to drive Counter Electrode of the chemical sensor

Pin Descriptions (continued)

Name	Pin	Description
CE	14	Counter Electrode. Output to drive Counter Electrode of the chemical sensor
DAP		Connect to AGND



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings⁽¹⁾⁽²⁾

ESD Tolerance ⁽³⁾	
Human Body Model	2kV
Charge-Device Model	1kV
Machine Model	200V
Voltage between any two pins	6.0V
Current through VDD or VSS	50mA
Current sunk and sourced by CE pin	10mA
Current out of other pins ⁽⁴⁾	5mA
Storage Temperature Range	-65°C to 150°C
Junction Temperature ⁽⁵⁾	150°C
For soldering specifications: see product folder at www.national.com and www.national.com/ms/MS/MS-SOLDERING.pdf	

- (1) "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Operating Ratings is not implied. Operating Ratings indicate conditions at which the device is functional and the device should not be operated beyond such conditions.
- (2) If Military/Aerospace specified devices are required, please contact the TI Sales Office/Distributors for availability and specifications.
- (3) Human Body Model, applicable std. MIL-STD-883, Method 3015.7. Machine Model, applicable std. JESD22-A115-A (ESD MM std. of JEDEC) Field- Induced Charge-Device Model, applicable std. JESD22-C101-C (ESD FICDM std. of JEDEC).
- (4) All non-power pins of this device are protected against ESD by snapback devices. Voltage at such pins will rise beyond absmax if current is forced into pin.
- (5) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and the ambient temperature, T_A . The maximum allowable power dissipation at any ambient temperature is $P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$. All numbers apply for packages soldered directly onto a PC board.

Operating Ratings⁽¹⁾

Supply Voltage V_S =(VDD - AGND)	2.7V to 5.25V
Temperature Range ⁽²⁾	-40°C to 85°C
Package Thermal Resistance ⁽²⁾	
14-Pin WSON (θ_{JA})	44 °C/W

- (1) "Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Operating Ratings is not implied. Operating Ratings indicate conditions at which the device is functional and the device should not be operated beyond such conditions.
- (2) The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and the ambient temperature, T_A . The maximum allowable power dissipation at any ambient temperature is $P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$. All numbers apply for packages soldered directly onto a PC board.

Electrical Characteristics ⁽¹⁾

Unless otherwise specified, all limits guaranteed for $T_A = 25^\circ\text{C}$, $V_S = (V_{DD} - \text{AGND})$, $V_S = 3.3\text{V}$ and $\text{AGND} = \text{DGND} = 0\text{V}$, $V_{\text{REF}} = 2.5\text{V}$, Internal Zero = 20% V_{REF} . **Boldface** limits apply at the temperature extremes.

Parameter		Test Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units
POWER SUPPLY SPECIFICATION						
I _S	Supply Current	3-lead amperometric cell mode MODECN = 0x03		10	15 13.5	μA
		Standby mode MODECN = 0x02		6.5	10 8	
		Temperature Measurement mode with TIA OFF MODECN = 0x06		11.4	15 13.5	
		Temperature Measurement mode with TIA ON MODECN = 0x07		14.9	20 18	
		2-lead ground referred galvanic cell mode VREF=1.5V MODECN = 0x01		6.2	9 8	
		Deep Sleep mode MODECN = 0x00		0.6	1 0.85	
POTENTIOSTAT						
Bias_RW	Bias Programming range (differential voltage between RE pin and WE pin)	Percentage of voltage referred to VREF or VDD		±24		%
	Bias Programming Resolution	First two smallest step		±1		%
		All other steps		±2		
I _{RE}	Input bias current at RE pin	VDD=2.7V; Internal Zero 50% VDD	-90 -800		90 800	pA
		VDD=5.25V; Internal Zero 50% VDD	-90 -900		90 900	
I _{CE}	Minimum operating current capability	sink		750		μA
		source		750		
	Minimum charging capability ⁽⁴⁾	sink		10		mA
		source		10		
AOL_A1	Open loop voltage gain of control loop op amp (A1)	300mV≤VCE≤Vs-300mV; -750μA≤ICE≤750μA	104	120		dB
en_RW	Low Frequency integrated noise between RE pin and WE pin	0.1Hz to 10Hz, Zero Bias ⁽⁵⁾		3.4		μVpp
		0.1Hz to 10Hz, with Bias ⁽⁵⁾ ⁽⁶⁾		5.1		

(1) Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No guarantee of parametric performance is indicated in the electrical tables under conditions of internal self-heating where $T_J > T_A$. Absolute Maximum Ratings indicate junction temperature limits beyond which the device may be permanently degraded, either mechanically or electrically.

(2) Limits are 100% production tested at 25°C . Limits over the operating temperature range are guaranteed through correlations using statistical quality control (SQC) method.

(3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.

(4) At such currents no accuracy of the output voltage can be expected.

(5) This parameter includes both A1 and TIA's noise contribution.

(6) In case of external reference connected, the noise of the reference has to be added.

Electrical Characteristics ⁽¹⁾ (continued)

Unless otherwise specified, all limits guaranteed for $T_A = 25^\circ\text{C}$, $V_S = (V_{DD} - \text{AGND})$, $V_S = 3.3\text{V}$ and $\text{AGND} = \text{DGND} = 0\text{V}$, $V_{REF} = 2.5\text{V}$, Internal Zero = 20% V_{REF} . **Boldface** limits apply at the temperature extremes.

Parameter		Test Conditions		Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units
V_{OS_RW}	WE Voltage Offset referred to RE	BIAS polarity ⁽⁷⁾	0% V_{REF} Internal Zero=20% V_{REF}	-550		550	μV
			0% V_{REF} Internal Zero=50% V_{REF}				
			0% V_{REF} Internal Zero=67% V_{REF}				
			$\pm 1\%$ V_{REF}	-575		575	
			$\pm 2\%$ V_{REF}	-610		610	
			$\pm 4\%$ V_{REF}	-750		750	
			$\pm 6\%$ V_{REF}	-840		840	
			$\pm 8\%$ V_{REF}	-930		930	
			$\pm 10\%$ V_{REF}	-1090		1090	
			$\pm 12\%$ V_{REF}	-1235		1235	
			$\pm 14\%$ V_{REF}	-1430		1430	
			$\pm 16\%$ V_{REF}	-1510		1510	
			$\pm 18\%$ V_{REF}	-1575		1575	
			$\pm 20\%$ V_{REF}	-1650		1650	
			$\pm 22\%$ V_{REF}	-1700		1700	
			$\pm 24\%$ V_{REF}	-1750		1750	
TcV_{OS_RW}	WE Voltage Offset Drift referred to RE from -40°C to 85°C ⁽⁸⁾	BIAS polarity ⁽⁷⁾	0% V_{REF} Internal Zero=20% V_{REF}	-4		4	$\mu\text{V}/^\circ\text{C}$
			0% V_{REF} Internal Zero=50% V_{REF}				
			0% V_{REF} Internal Zero=67% V_{REF}				
			$\pm 1\%$ V_{REF}	-4		4	
			$\pm 2\%$ V_{REF}	-4		4	
			$\pm 4\%$ V_{REF}	-5		5	
			$\pm 6\%$ V_{REF}	-5		5	
			$\pm 8\%$ V_{REF}	-5		5	
			$\pm 10\%$ V_{REF}	-6		6	
			$\pm 12\%$ V_{REF}	-6		6	
			$\pm 14\%$ V_{REF}	-7		7	
			$\pm 16\%$ V_{REF}	-7		7	
			$\pm 18\%$ V_{REF}	-8		8	
			$\pm 20\%$ V_{REF}	-8		8	
			$\pm 22\%$ V_{REF}	-8		8	
			$\pm 24\%$ V_{REF}	-8		8	

(7) For negative bias polarity the Internal Zero is set at 67% V_{REF} .

(8) Offset voltage temperature drift is determined by dividing the change in V_{OS} at the temperature extremes by the total temperature change. Starting from the measured voltage offset at temperature T_1 ($V_{OS_RW}(T_1)$), the voltage offset at temperature T_2 ($V_{OS_RW}(T_2)$) is calculated according the following formula: $V_{OS_RW}(T_2) = V_{OS_RW}(T_1) + \text{ABS}(T_2 - T_1) * TcV_{OS_RW}$.

Electrical Characteristics ⁽¹⁾ (continued)

Unless otherwise specified, all limits guaranteed for $T_A = 25^\circ\text{C}$, $V_S = (V_{DD} - \text{AGND})$, $V_S = 3.3\text{V}$ and $\text{AGND} = \text{DGND} = 0\text{V}$, $V_{REF} = 2.5\text{V}$, Internal Zero = 20% V_{REF} . **Boldface** limits apply at the temperature extremes.

Parameter		Test Conditions		Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units
TIA_GAIN	Transimpedance gain accuracy				5		%
	Linearity				±0.05		%
	Programmable TIA Gains	7 programmable gain resistors			2.75 3.5 7 14 35 120 350		kΩ
	Maximum external gain resistor			350			
TIA_ZV	Internal zero voltage	3 programmable percentages of VREF			20 50 67		%
		3 programmable percentages of VDD			20 50 67		
	Internal zero voltage Accuracy				±0.04		%
RL	Programmable Load	4 programmable resistive loads			10 33 50 100		Ω
	Load accuracy				5		%
PSRR	Power Supply Rejection Ratio at RE pin	2.7 ≤VDD≤5.25V	Internal zero 20% VREF	80	110		dB
			Internal zero 50% VREF				
			Internal zero 67% VREF				
TEMPERATURE SENSOR SPECIFICATION (Refer to Table 1 in the Function Description for details)							
	Temperature Error	TA=−40°C to 85°C		−3		3	°C
	Sensitivity	TA=−40°C to 85°C			−8.2		mV/°C
	Power on time					1.9	ms
EXTERNAL REFERENCE SPECIFICATION							
VREF	External Voltage reference range			1.5		VDD	V
	Input impedance				10		MΩ

I²C Interface ⁽¹⁾

Unless otherwise specified, all limits guaranteed for $T_A = 25^\circ\text{C}$, $V_S = (V_{DD} - \text{AGND})$, $2.7\text{V} < V_S < 5.25\text{V}$ and $\text{AGND} = \text{DGND} = 0\text{V}$, $V_{REF} = 2.5\text{V}$. **Boldface** limits apply at the temperature extremes

Parameter		Test Conditions	Min ⁽²⁾	Typ ⁽³⁾	Max ⁽²⁾	Units
V_{IH}	Input High Voltage		0.7*VDD			V
V_{IL}	Input Low Voltage				0.3*VDD	V
V_{OL}	Output Low Voltage	$I_{OUT} = 3\text{mA}$			0.4	V
	Hysteresis ⁽⁴⁾		0.1*VDD			V
C_{IN}	Input Capacitance on all digital pins			0.5		pF

- (1) Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No guarantee of parametric performance is indicated in the electrical tables under conditions of internal self-heating where $T_J > T_A$. Absolute Maximum Ratings indicate junction temperature limits beyond which the device may be permanently degraded, either mechanically or electrically.
- (2) Limits are 100% production tested at 25°C . Limits over the operating temperature range are guaranteed through correlations using statistical quality control (SQC) method.
- (3) Typical values represent the most likely parametric norm as determined at the time of characterization. Actual typical values may vary over time and will also depend on the application and configuration. The typical values are not tested and are not guaranteed on shipped production material.
- (4) This parameter is guaranteed by design or characterization.

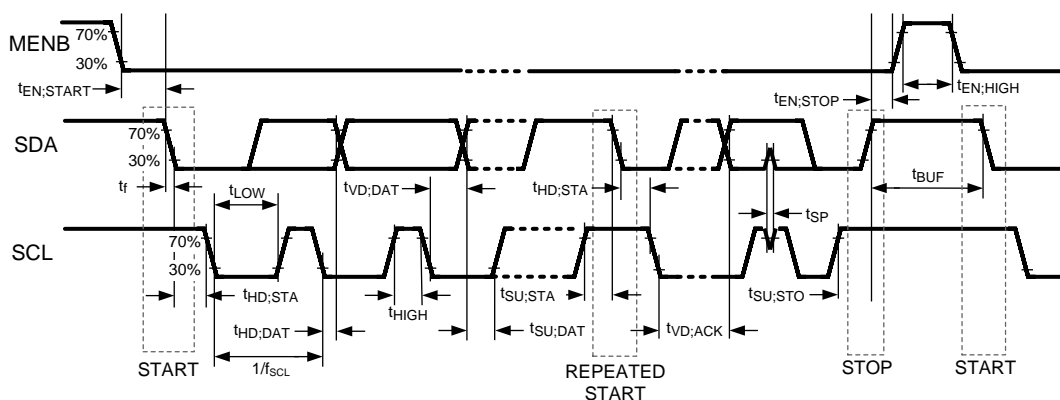
Timing Characteristics ⁽¹⁾

Unless otherwise specified, all limits guaranteed for $T_A = 25^\circ\text{C}$, $V_S = (V_{DD} - AGND)$, $V_S = 3.3\text{V}$ and $AGND = DGND = 0\text{V}$, $V_{REF} = 2.5\text{V}$, Internal Zero = 20% V_{REF} . **Boldface** limits apply at the temperature extremes. Refer to [Timing Diagram](#).

Parameter		Test Conditions	Min	Typ	Max	Units
f_{SCL}	Clock Frequency		10		100	kHz
t_{LOW}	Clock Low Time		4.7			μs
t_{HIGH}	Clock High Time		4.0			μs
$t_{HD;STA}$	Data valid	After this period, the first clock pulse is generated	4.0			μs
$t_{SU;STA}$	Set-up time for a repeated START condition		4.7			μs
$t_{HD;DAT}$	Data hold time ⁽²⁾		0			ns
$t_{SU;DAT}$	Data Setup time		250			ns
t_f	SDA fall time ⁽³⁾	$I_L \leq 3\text{mA}$; $CL \leq 400\text{pF}$			250	ns
$t_{SU;STO}$	Set-up time for STOP condition		4.0			μs
t_{BUF}	Bus free time between a STOP and START condition		4.7			μs
$t_{VD;DAT}$	Data valid time				3.45	μs
$t_{VD;ACK}$	Data valid acknowledge time				3.45	μs
t_{SP}	Pulse width of spikes that must be suppressed by the input filter ⁽³⁾				50	ns
$t_{timeout}$	SCL and SDA Timeout		25		100	ms
$t_{EN;START}$	I ² C Interface Enabling		600			ns
$t_{EN;STOP}$	I ² C Interface Disabling		600			ns
$t_{EN;HIGH}$	time between consecutive I ² C interface enabling and disabling		600			ns

- (1) Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No guarantee of parametric performance is indicated in the electrical tables under conditions of internal self-heating where $T_J > T_A$. Absolute Maximum Ratings indicate junction temperature limits beyond which the device may be permanently degraded, either mechanically or electrically.
- (2) LMP91000 provides an internal 300ns minimum hold time to bridge the undefined region of the falling edge of SCL.
- (3) This parameter is guaranteed by design or characterization.

TIMING DIAGRAM



Typical Performance Characteristics

Unless otherwise specified, $T_A = 25^\circ\text{C}$, $V_S = (V_{DD} - \text{AGND})$, $2.7\text{V} < V_S < 5.25\text{V}$ and $\text{AGND} = \text{DGND} = 0\text{V}$, $V_{\text{REF}} = 2.5\text{V}$.

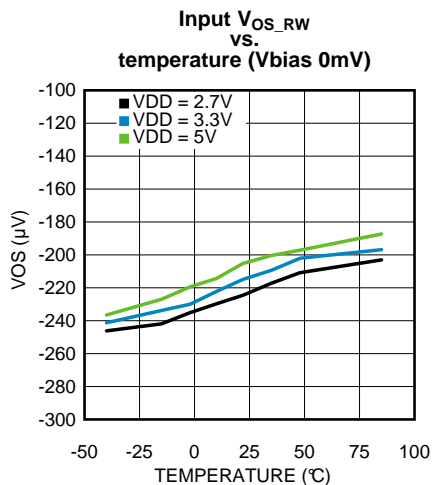


Figure 3.

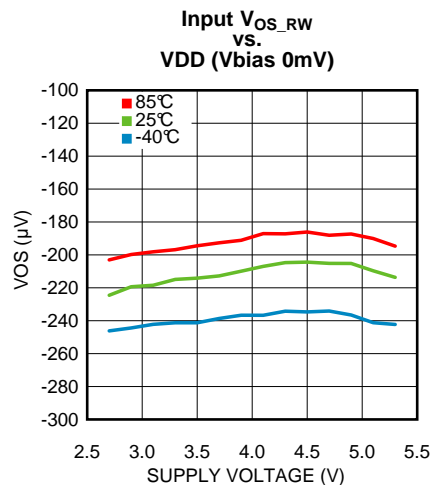


Figure 4.

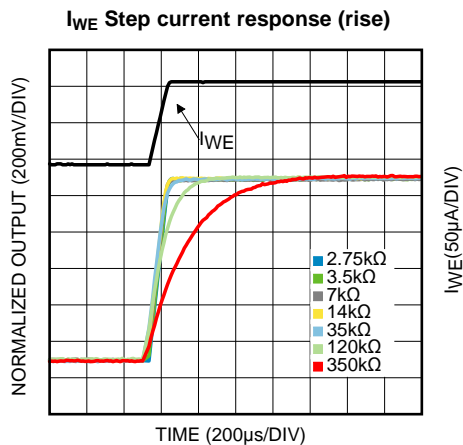


Figure 5.

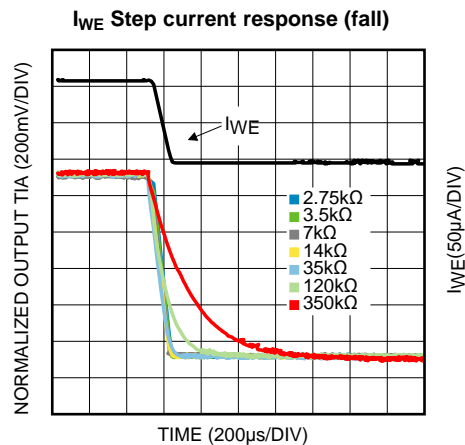


Figure 6.

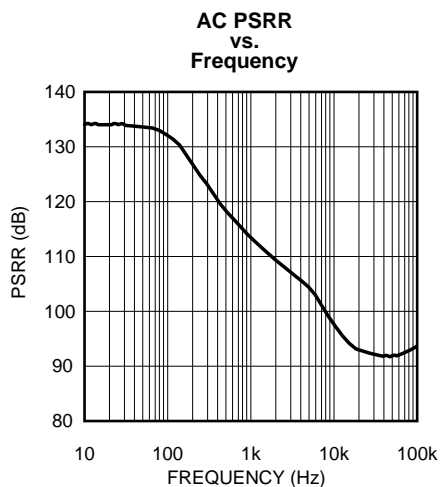


Figure 7.

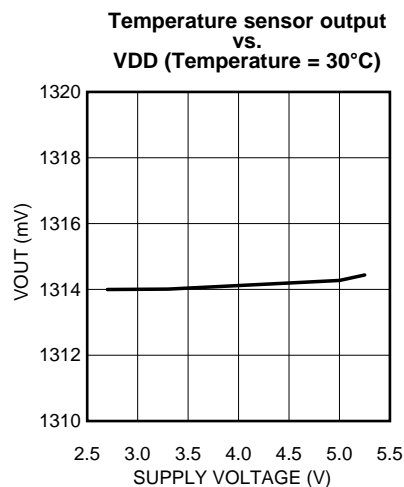


Figure 8.

Typical Performance Characteristics (continued)

Unless otherwise specified, $T_A = 25^\circ\text{C}$, $V_S = (V_{DD} - \text{AGND})$, $2.7\text{V} < V_S < 5.25\text{V}$ and $\text{AGND} = \text{DGND} = 0\text{V}$, $V_{REF} = 2.5\text{V}$.

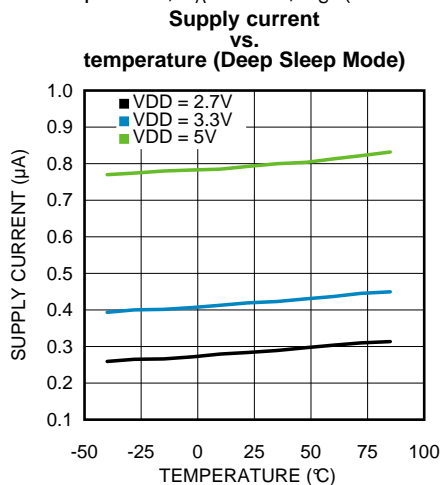


Figure 9.

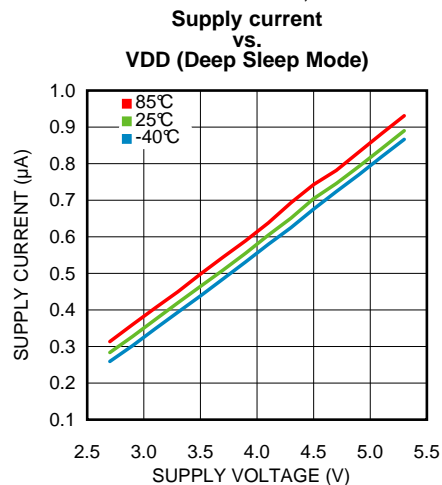


Figure 10.

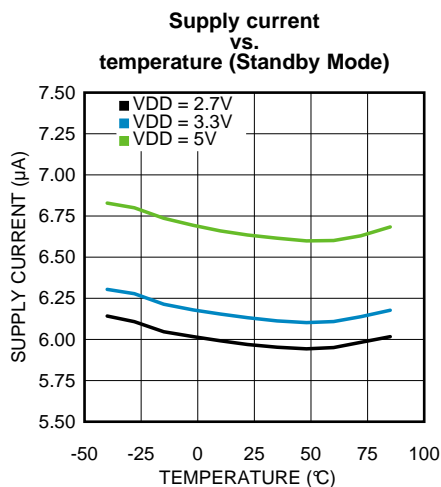


Figure 11.

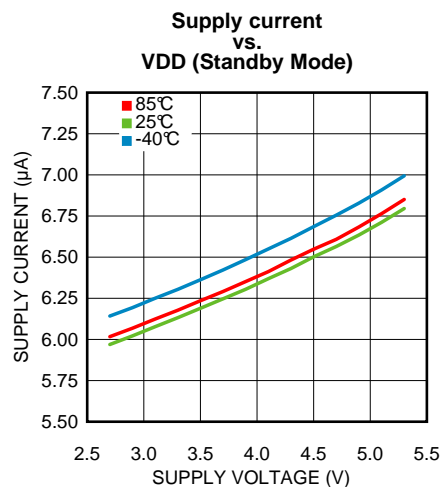


Figure 12.

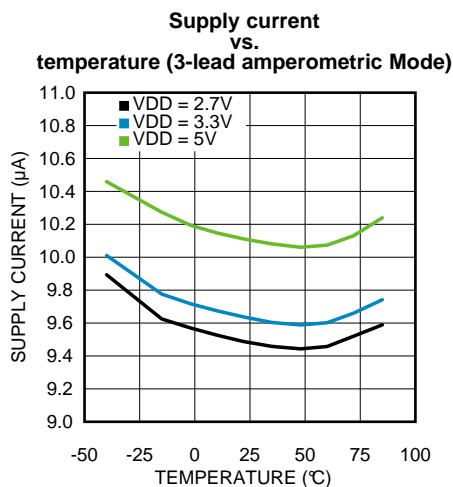


Figure 13.

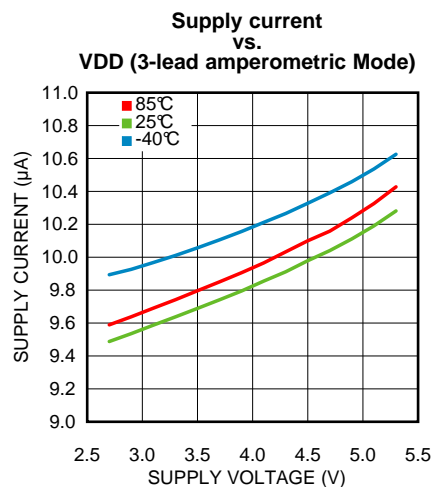


Figure 14.

Typical Performance Characteristics (continued)

Unless otherwise specified, $T_A = 25^\circ\text{C}$, $V_S = (V_{DD} - \text{AGND})$, $2.7\text{V} < V_S < 5.25\text{V}$ and $\text{AGND} = \text{DGND} = 0\text{V}$, $V_{\text{REF}} = 2.5\text{V}$.

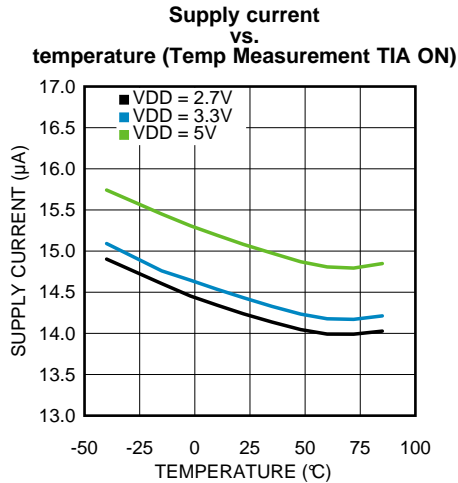


Figure 15.

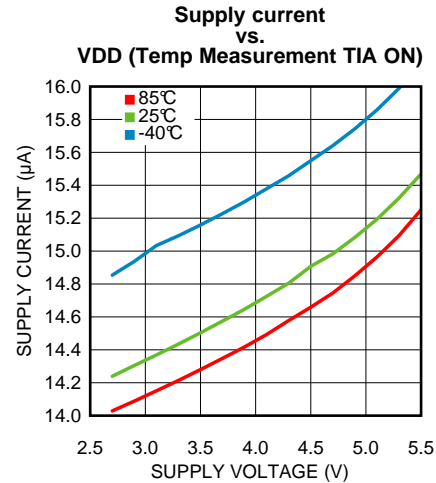


Figure 16.

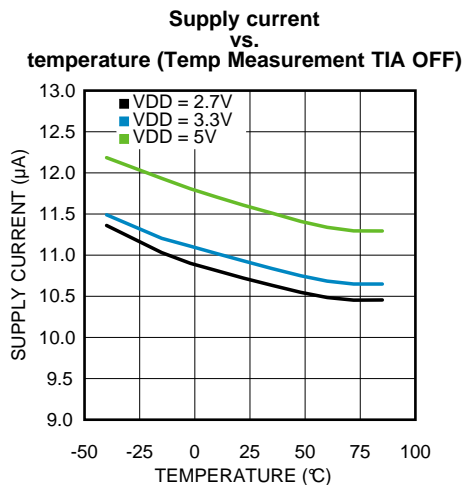


Figure 17.

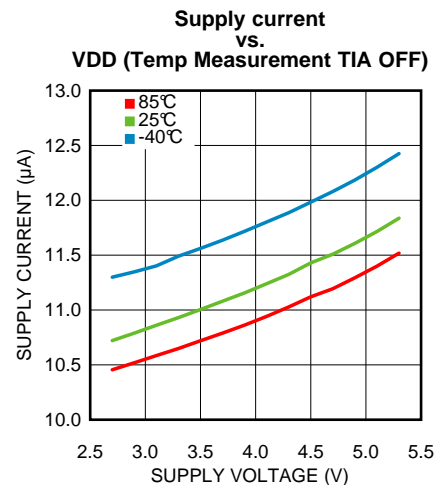


Figure 18.

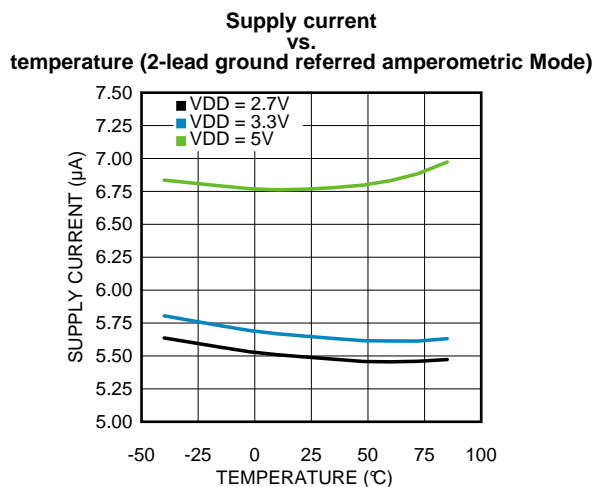


Figure 19.

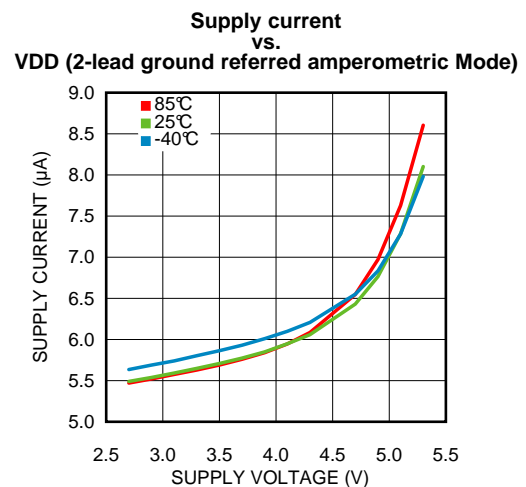


Figure 20.

Typical Performance Characteristics (continued)

Unless otherwise specified, $T_A = 25^\circ\text{C}$, $V_S = (V_{DD} - \text{AGND})$, $2.7\text{V} < V_S < 5.25\text{V}$ and $\text{AGND} = \text{DGND} = 0\text{V}$, $V_{REF} = 2.5\text{V}$.

0.1Hz to 10Hz noise, 0V bias

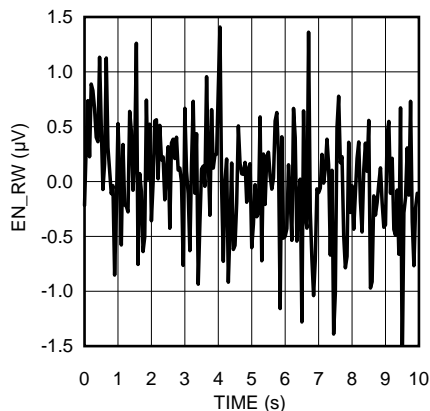


Figure 21.

0.1Hz to 10Hz noise, 300mV bias

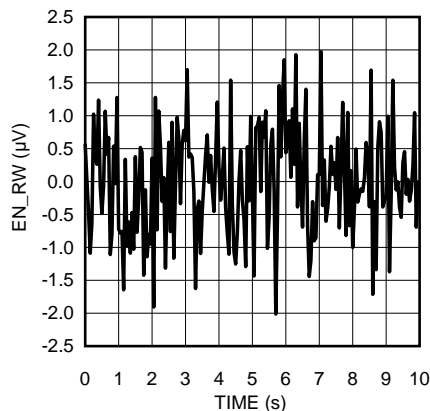


Figure 22.

0.1Hz to 10Hz noise, 600mV bias

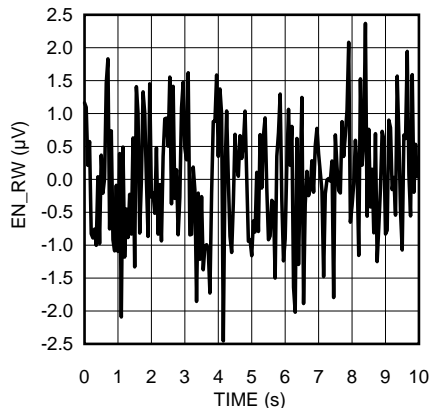


Figure 23.

A V_{OUT} step response 100 ppm to 400 ppm CO
(CO gas sensor connected to LMP91000)

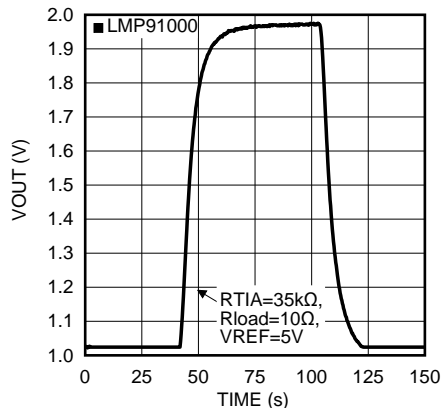


Figure 24.

FUNCTION DESCRIPTION

GENERAL

The LMP91000 is a programmable AFE for use in micropower chemical sensing applications. The LMP91000 is designed for 3-lead single gas sensors and for 2-lead galvanic cell sensors. This device provides all of the functionality for detecting changes in gas concentration based on a delta current at the working electrode. The LMP91000 generates an output voltage proportional to the cell current. Transimpedance gain is user programmable through an I²C compatible interface from 2.75k Ω to 350k Ω making it easy to convert current ranges from 5 μ A to 750 μ A full scale. Optimized for micro-power applications, the LMP91000 AFE works over a voltage range of 2.7V to 5.25 V. The cell voltage is user selectable using the on board programmability. In addition, it is possible to connect an external transimpedance gain resistor. A temperature sensor is embedded and it can be power cycled through the interface. The output of this temperature sensor can be read by the user through the VOUT pin. It is also possible to have both temperature output and output of the TIA at the same time; the pin C2 is internally connected to the output of the transimpedance (TIA), while the temperature is available at the VOUT pin. Depending on the configuration, total current consumption for the device can be less than 10 μ A. For power savings, the transimpedance amplifier can be turned off and instead a load impedance equivalent to the TIA's inputs impedance is switched in.

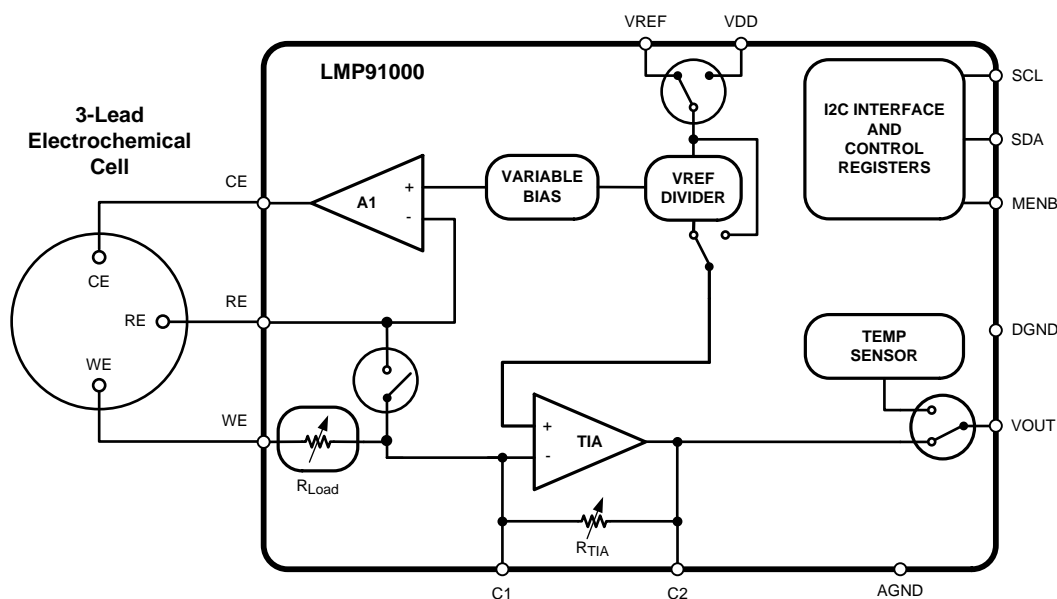


Figure 25. System Block Diagram

POTENTIOSTAT CIRCUITRY

The core of the LMP91000 is a potentiostat circuit. It consists of a differential input amplifier used to compare the potential between the working and reference electrodes to a required working bias potential (set by the **Variable Bias circuitry**). The error signal is amplified and applied to the counter electrode (through the **Control Amplifier - A1**). Any changes in the impedance between the working and reference electrodes will cause a change in the voltage applied to the counter electrode, in order to maintain the constant voltage between working and reference electrodes. A **Transimpedance Amplifier** connected to the working electrode, is used to provide an output voltage that is proportional to the cell current. The working electrode is held at virtual ground (**Internal ground**) by the transimpedance amplifier. The potentiostat will compare the reference voltage to the desired bias potential and adjust the voltage at the counter electrode to maintain the proper working-to-reference voltage.

Transimpedance amplifier

The transimpedance amplifier (TIA in Figure 25) has 7 programmable internal gain resistors. This accommodates the full scale ranges of most existing sensors. Moreover an external gain resistor can be connected to the LMP91000 between C1 and C2 pins. The gain is set through the I²C interface.

Control amplifier

The control amplifier (A1 op amp in [Figure 25](#)) has two tasks: a) providing initial charge to the sensor, b) providing a bias voltage to the sensor. A1 has the capability to drive up to 10mA into the sensor in order to provide a fast initial conditioning. A1 is able to sink and source current according to the connected gas sensor (reducing or oxidizing gas sensor). It can be powered down to reduce system power consumption. However powering down A1 is not recommended, as it may take a long time for the sensor to recover from this situation.

Variable Bias

The Variable Bias block circuitry ([Figure 25](#)) provides the amount of bias voltage required by a biased gas sensor between its reference and working electrodes. The bias voltage can be programmed to be 1% to 24% (14 steps in total) of the supply, or of the external reference voltage. The 14 steps can be programmed through the I²C interface. The polarity of the bias can be also programmed.

Internal zero

The internal Zero is the voltage at the non-inverting pin of the TIA. The internal zero can be programmed to be either 67%, 50% or 20%, of the supply, or the external reference voltage. This provides both sufficient headroom for the counter electrode of the sensor to swing, in case of sudden changes in the gas concentration, and best use of the ADC's full scale input range.

The Internal zero is provided through an internal voltage divider (Vref divider box in [Figure 25](#)). The divider is programmed through the I²C interface.

Temperature sensor

The embedded temperature sensor can be switched off during gas concentration measurement to save power. The temperature measurement is triggered through the I²C interface. The temperature output is available at the VOUT pin until the configuration bit is reset. The output signal of the temperature sensor is a voltage, referred to the ground of the LMP91000 (AGND).

Table 1. Temperature Sensor Transfer

Temperature (°C)	Output Voltage (mV)	Temperature (°C)	Output Voltage (mV)
-40	1875	23	1375
-39	1867	24	1367
-38	1860	25	1359
-37	1852	26	1351
-36	1844	27	1342
-35	1836	28	1334
-34	1828	29	1326
-33	1821	30	1318
-32	1813	31	1310
-31	1805	32	1302
-30	1797	33	1293
-29	1789	34	1285
-28	1782	35	1277
-27	1774	36	1269
-26	1766	37	1261
-25	1758	38	1253
-24	1750	39	1244
-23	1742	40	1236
-22	1734	41	1228
-21	1727	42	1220
-20	1719	43	1212
-19	1711	44	1203
-18	1703	45	1195

Table 1. Temperature Sensor Transfer (continued)

-17	1695	46	1187
-16	1687	47	1179
-15	1679	48	1170
-14	1671	49	1162
-13	1663	50	1154
-12	1656	51	1146
-11	1648	52	1137
-10	1640	53	1129
-9	1632	54	1121
-8	1624	55	1112
-7	1616	56	1104
-6	1608	57	1096
-5	1600	58	1087
-4	1592	59	1079
-3	1584	60	1071
-2	1576	61	1063
-1	1568	62	1054
0	1560	63	1046
1	1552	64	1038
2	1544	65	1029
3	1536	66	1021
4	1528	67	1012
5	1520	68	1004
6	1512	69	996
7	1504	70	987
8	1496	71	979
9	1488	72	971
10	1480	73	962
11	1472	74	954
12	1464	75	945
13	1456	76	937
14	1448	77	929
15	1440	78	920
16	1432	79	912
17	1424	80	903
18	1415	81	895
19	1407	82	886
20	1399	83	878
21	1391	84	870
22	1383	85	861

Although the temperature sensor is very linear, its response does have a slight downward parabolic shape. This shape is very accurately reflected in Table 1. For a linear approximation, a line can easily be calculated over the desired temperature range from Table 1 using the two-point equation:

$$V - V_1 = ((V_2 - V_1) / (T_2 - T_1)) * (T - T_1)$$

Where V is in mV, T is in °C, T₁ and V₁ are the coordinates of the lowest temperature, T₂ and V₂ are the coordinates of the highest temperature.

For example, if we want to determine the equation of a line over a temperature range of 20°C to 50°C, we would proceed as follows:

$$V-1399\text{mV} = ((1154\text{mV} - 1399\text{mV}) / (50^{\circ}\text{C} - 20^{\circ}\text{C})) * (T - 20^{\circ}\text{C})$$

$$V-1399\text{mV} = -8.16\text{mV}/^{\circ}\text{C} * (T - 20^{\circ}\text{C})$$

$$V = (-8.16\text{mV}/^{\circ}\text{C}) * T + 1562.2\text{mV}$$

Using this method of linear approximation, the transfer function can be approximated for one or more temperature ranges of interest.

I²C INTERFACE

The I²C compatible interface operates in Standard mode (100kHz). Pull-up resistors or current sources are required on the SCL and SDA pins to pull them high when they are not being driven low. A logic zero is transmitted by driving the output low. A logic high is transmitted by releasing the output and allowing it to be pulled-up externally. The appropriate pull-up resistor values will depend upon the total bus capacitance and operating speed. The LMP91000 comes with a 7 bit bus fixed address: 1001 000.

WRITE AND READ OPERATION

In order to start any read or write operation with the LMP91000, MENB needs to be set low during the whole communication. Then the master generates a start condition by driving SDA from high to low while SCL is high. The start condition is always followed by a 7-bit slave address and a Read/Write bit. After these 8 bits have been transmitted by the master, SDA is released by the master and the LMP91000 either ACKs or NACKs the address. If the slave address matches, the LMP91000 ACKs the master. If the address doesn't match, the LMP91000 NACKs the master. For a write operation, the master follows the ACK by sending the 8-bit register address pointer. Then the LMP91000 ACKs the transfer by driving SDA low. Next, the master sends the 8-bit data to the LMP91000. Then the LMP91000 ACKs the transfer by driving SDA low. At this point the master should generate a stop condition and optionally set the MENB at logic high level (refer to [Figure 26](#), [Figure 27](#), and [Figure 28](#)).

A read operation requires the LMP91000 address pointer to be set first, also in this case the master needs setting at low logic level the MENB, then the master needs to write to the device and set the address pointer before reading from the desired register. This type of read requires a start, the slave address, a write bit, the address pointer, a Repeated Start (if appropriate), the slave address, and a read bit (refer to [Figure 26](#), [Figure 27](#), and [Figure 28](#)). Following this sequence, the LMP91000 sends out the 8-bit data of the register.

When just one LMP91000 is present on the I²C bus the MENB can be tied to ground (low logic level).

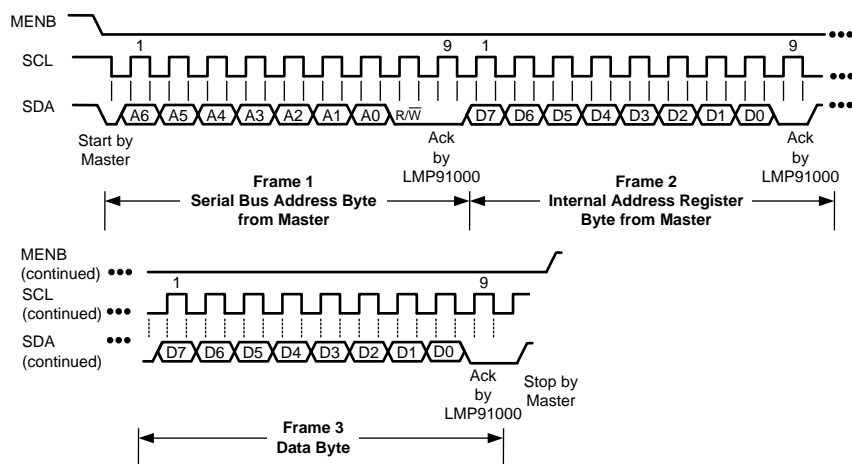


Figure 26. Register Write Transaction

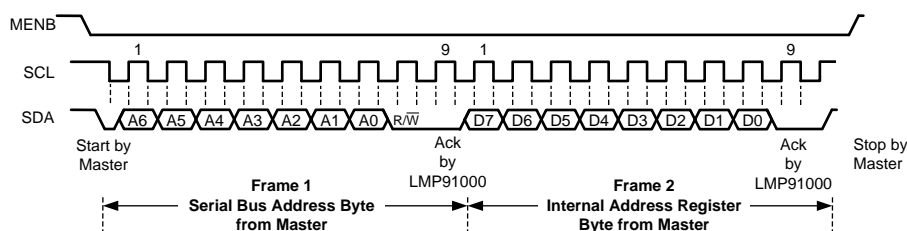


Figure 27. Pointer Set Transaction

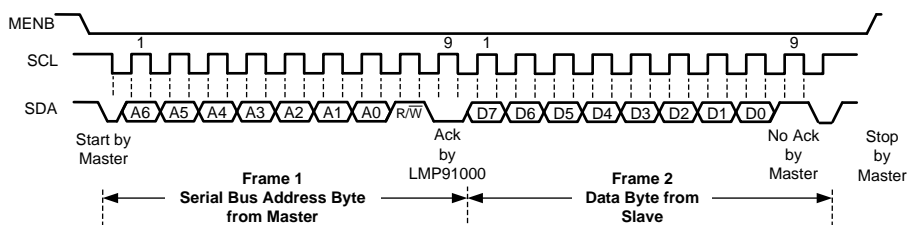


Figure 28. Register Read Transaction

TIMEOUT FEATURE

The timeout is a safety feature to avoid bus lockup situation. If SCL is stuck low for a time exceeding t_{timeout} , the LMP91000 will automatically reset its I²C interface. Also, in the case the LMP91000 hangs the SDA for a time exceeding t_{timeout} , the LMP91000's I²C interface will be reset so that the SDA line will be released. Since the SDA is an open-drain with an external resistor pull-up, this also avoids high power consumption when LMP91000 is driving the bus and the SCL is stopped.

REGISTERS

The registers are used to configure the LMP91000.

If writing to a reserved bit, user must write only 0. Readback value is unspecified and should be discarded.

Table 2. Register map

Address	Name	Power on default	Access	Lockable?
0x00	STATUS	0x00	Read only	N
0x01	LOCK	0x01	R/W	N
0x02 through 0x09	RESERVED			
0x10	TIACN	0x03	R/W	Y
0x11	REFCN	0x20	R/W	Y
0x12	MODECN	0x00	R/W	N
0x13 through 0xFF	RESERVED			

STATUS -- Status Register (address 0x00)

The status bit is an indication of the LMP91000's power-on status. If its readback is "0", the LMP91000 is not ready to accept other I²C commands.

Bit	Name	Function
[7:1]	RESERVED	
0	STATUS	Status of Device 0 Not Ready (default) 1 Ready

LOCK -- Protection Register (address 0x01)

The lock bit enables and disables the writing of the TIACN and the REFCN registers. In order to change the content of the TIACN and the REFCN registers the lock bit needs to be set to "0".

Bit	Name	Function
[7:1]	RESERVED	
0	LOCK	Write protection 0 Registers 0x10, 0x11 in write mode 1 Registers 0x10, 0x11 in read only mode (default)

TIACN -- TIA Control Register (address 0x10)

The parameters in the TIA control register allow the configuration of the transimpedance gain (R_{TIA}) and the load resistance (R_{Load}).

Bit	Name	Function
[7:5]	RESERVED	RESERVED
[4:2]	TIA_GAIN	TIA feedback resistance selection 000 External resistance (default) 001 2.75k Ω 010 3.5k Ω 011 7k Ω 100 14k Ω 101 35k Ω 110 120k Ω 111 350k Ω
[1:0]	RLOAD	R_{Load} selection 00 10 Ω 01 33 Ω 10 50 Ω 11 100Ω (default)

REFCN -- Reference Control Register (address 0x11)

The parameters in the Reference control register allow the configuration of the Internal zero, Bias and Reference source. When the Reference source is external, the reference is provided by a reference voltage connected to the VREF pin. In this condition the Internal Zero and the Bias voltage are defined as a percentage of VREF voltage instead of the supply voltage.

Bit	Name	Function
7	REF_SOURCE	Reference voltage source selection 0 Internal (default) 1 external
[6:5]	INT_Z	Internal zero selection (Percentage of the source reference) 00 20% 01 50% (default) 10 67% 11 Internal zero circuitry bypassed (only in O ₂ ground referred measurement)
4	BIAS_SIGN	Selection of the Bias polarity 0 Negative ($V_{WE} - V_{RE}$) < 0V (default) 1 Positive ($V_{WE} - V_{RE}$) > 0V

Bit	Name	Function
[3:0]	BIAS	BIAS selection (Percentage of the source reference) 0000 0% (default) 0001 1% 0010 2% 0011 4% 0100 6% 0101 8% 0110 10% 0111 12% 1000 14% 1001 16% 1010 18% 1011 20% 1100 22% 1101 24%

MODECN -- Mode Control Register (address 0x12)

The Parameters in the Mode register allow the configuration of the Operation Mode of the LMP91000.

Bit	Name	Function
7	FET_SHORT	Shorting FET feature 0 Disabled (default) 1 Enabled
[6:3]	RESERVED	
[2:0]	OP_MODE	Mode of Operation selection 000 Deep Sleep (default) 001 2-lead ground referred galvanic cell 010 Standby 011 3-lead amperometric cell 110 Temperature measurement (TIA OFF) 111 Temperature measurement (TIA ON)

When the LMP91000 is in Temperature measurement (TIA ON) mode, the output of the temperature sensor is present at the VOUT pin, while the output of the potentiostat circuit is available at pin C2.

GAS SENSOR INTERFACE

The LMP91000 supports both 3-lead and 2-lead gas sensors. Most of the toxic gas sensors are amperometric cells with 3 leads (Counter, Worker and Reference). These leads should be connected to the LMP91000 in the potentiostat topology. The 2-lead gas sensor (known as galvanic cell) should be connected as simple buffer either referred to the ground of the system or referred to a reference voltage. The LMP91000 support both connections for 2-lead gas sensor.

3-lead Amperometric Cell In Potentiostat Configuration

Most of the amperometric cell have 3 leads (Counter, Reference and Working electrodes). The interface of the 3-lead gas sensor to the LMP91000 is straightforward, the leads of the gas sensor need to be connected to the namesake pins of the LMP91000.

The LMP91000 is then configured in 3-lead amperometric cell mode; in this configuration the Control Amplifier (A1) is ON and provides the internal zero voltage and bias in case of biased gas sensor. The transimpedance amplifier (TIA) is ON, it converts the current generated by the gas sensor in a voltage, according to the transimpedance gain:

$$\text{Gain} = R_{\text{TIA}}$$

If different gains are required, an external resistor can be connected between the pins C1 and C2. In this case the internal feedback resistor should be programmed to "external". The R_{Load} together with the output capacitance of the gas sensor acts as a low pass filter.

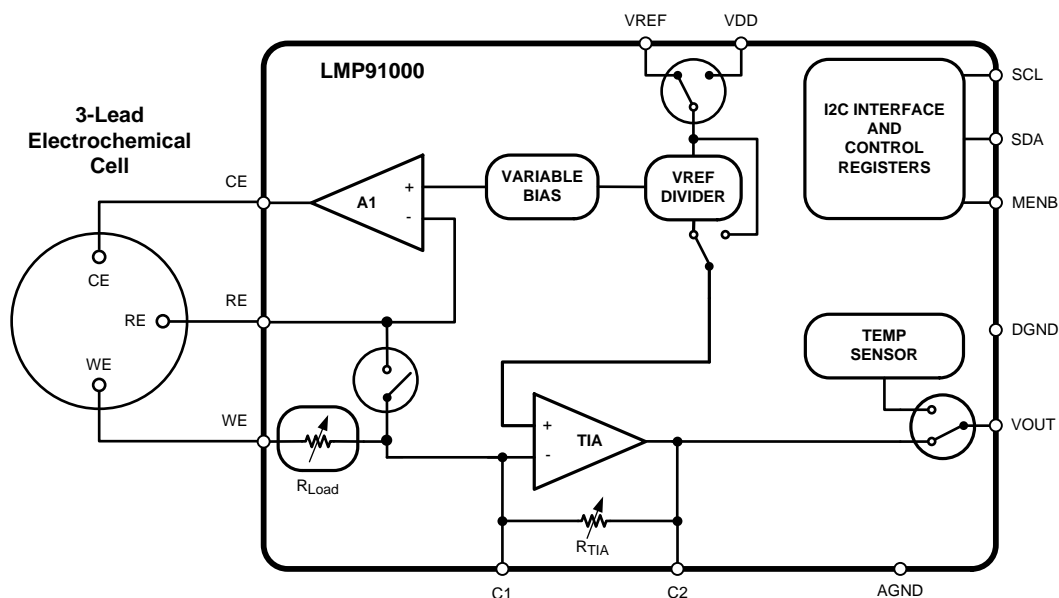


Figure 29. 3-Lead Amperometric Cell

2-lead Galvanic Cell In Ground Referred Configuration

When the LMP91000 is interfaced to a galvanic cell (for instance to an Oxygen gas sensor) referred to the ground of the system, an external resistor needs to be placed in parallel to the gas sensor; the negative electrode of the gas sensor is connected to the ground of the system and the positive electrode to the Vref pin of the LMP91000, the working pin of the LMP91000 is connected to the ground.

The LMP91000 is then configured in 2-lead galvanic cell mode and the Vref bypass feature needs to be enabled. In this configuration the Control Amplifier (A1) is turned off, and the output of the gas sensor is amplified by the Transimpedance Amplifier (TIA) which is configured as a simple non-inverting amplifier.

The gain of this non inverting amplifier is set according the following formula

$$\text{Gain} = 1 + (R_{TIA} / R_{Load})$$

If different gains are required, an external resistor can be connected between the pins C1 and C2. In this case the internal feedback resistor should be programmed to "external".

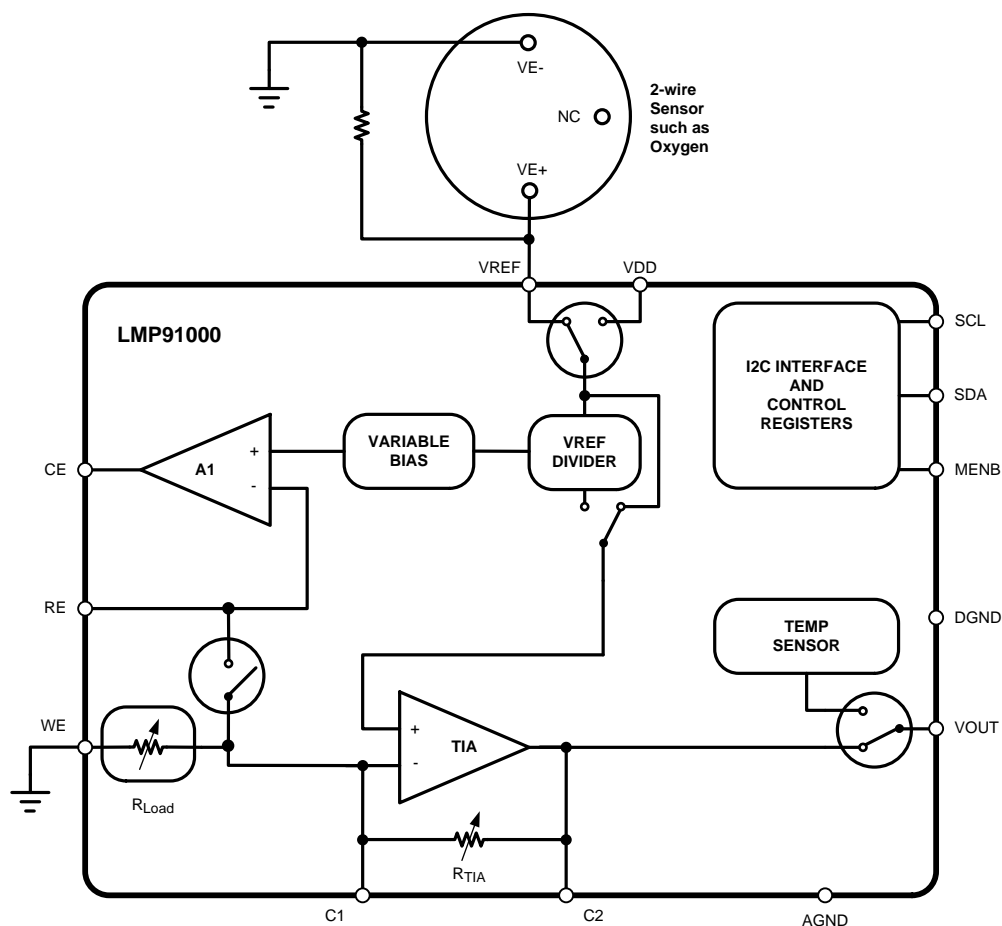


Figure 30. 2-Lead Galvanic Cell Ground Referred

2-lead Galvanic Cell In Potentiostat Configuration

When the LMP91000 is interfaced to a galvanic cell (for instance to an Oxygen gas sensor) referred to a reference, the Counter and the Reference pin of the LMP91000 are shorted together and connected to negative electrode of the galvanic cell. The positive electrode of the galvanic cell is then connected to the Working pin of the LMP91000.

The LMP91000 is then configured in 3-lead amperometric cell mode (as for amperometric cell). In this configuration the Counter Amplifier (A1) is ON and provides the internal zero voltage. The transimpedance amplifier (TIA) is also ON, it converts the current generated by the gas sensor in a voltage, according to the transimpedance gain:

$$\text{Gain} = R_{TIA}$$

If different gains are required, an external resistor can be connected between the pins C1 and C2. In this case the internal feedback resistor should be programmed to "external".

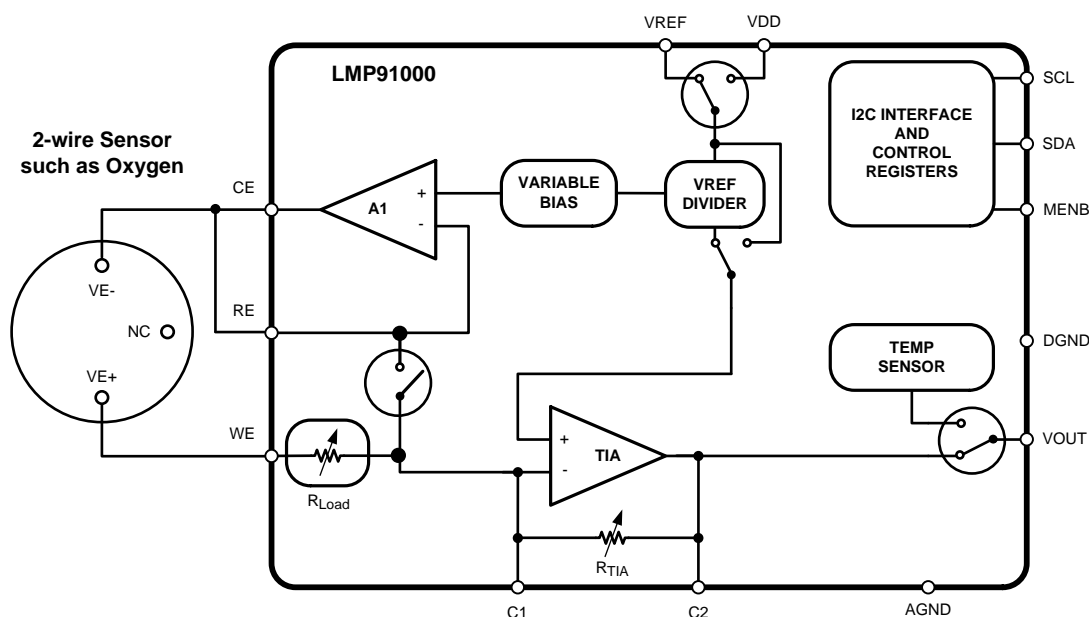


Figure 31. 2-Lead Galvanic Cell In Potentiostat Configuration

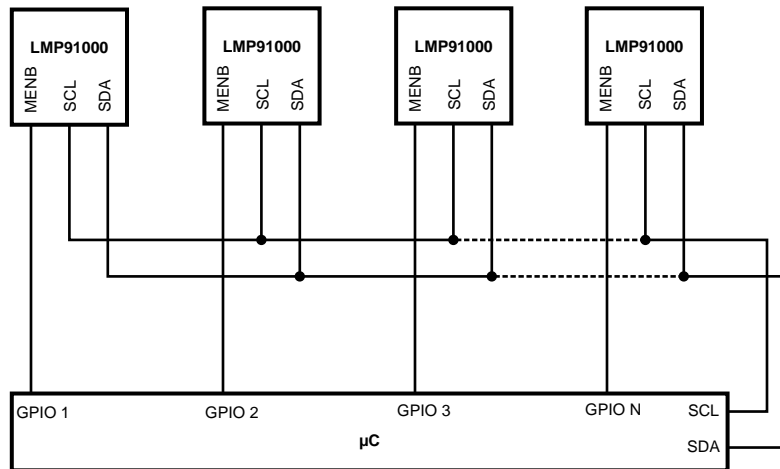
APPLICATION INFORMATION

CONNECTION OF MORE THAN ONE LMP91000 TO THE I²C BUS

The LMP91000 comes out with a unique and fixed I²C slave address. It is still possible to connect more than one LMP91000 to an I²C bus and select each device using the MENB pin. The MENB simply enables/disables the I²C communication of the LMP91000. When the MENB is at logic level low all the I²C communication is enabled, it is disabled when MENB is at high logic level.

In a system based on a μ controller and more than one LMP91000 connected to the I²C bus, the I²C lines (SDA and SCL) are shared, while the MENB of each LMP91000 is connected to a dedicate GPIO port of the μ controller.

The μ controller starts communication asserting one out of N MENB signals where N is the total number of LMP91000s connected to the I²C bus. Only the enabled device will acknowledge the I²C commands. After finishing communicating with this particular LMP91000, the microcontroller de-asserts the corresponding MENB and repeats the procedure for other LMP91000s. [Figure 32](#) shows the typical connection when more than one LMP91000 is connected to the I²C bus.

Figure 32. More than one LMP91000 on I²C bus

SMART GAS SENSOR ANALOG FRONT END

The LMP91000 together with an external EEPROM represents the core of a SMART GAS SENSOR AFE. In the EEPROM it is possible to store the information related to the GAS sensor type, calibration and LMP91000's configuration (content of registers 10h, 11h, 12h). At startup the microcontroller reads the EEPROM's content and configures the LMP91000. A typical smart gas sensor AFE is shown in Figure 33. The connection of MENB to the hardware address pin A0 of the EEPROM allows the microcontroller to select the LMP91000 and its corresponding EEPROM when more than one smart gas sensor AFE is present on the I²C bus. Note: only EEPROM I²C addresses with A0=0 should be used in this configuration.

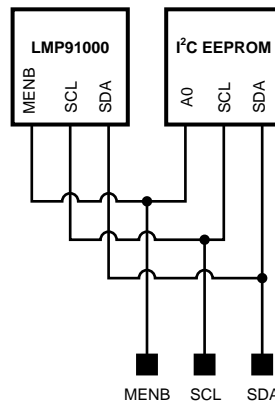


Figure 33. SMART GAS SENSOR AFE

SMART GAS SENSOR AFES ON I²C BUS

The connection of Smart gas sensor AFEs on the I²C bus is the natural extension of the previous concepts. Also in this case the microcontroller starts communication asserting 1 out of N MENB signals where N is the total number of smart gas sensor AFE connected to the I²C bus. Only one of the devices (either LMP91000 or its corresponding EEPROM) in the smart gas sensor AFE enabled will acknowledge the I²C commands. When the communication with this particular module ends, the microcontroller de-asserts the corresponding MENB and repeats the procedure for other modules. Figure 34 shows the typical connection when several smart gas sensor AFEs are connected to the I²C bus.

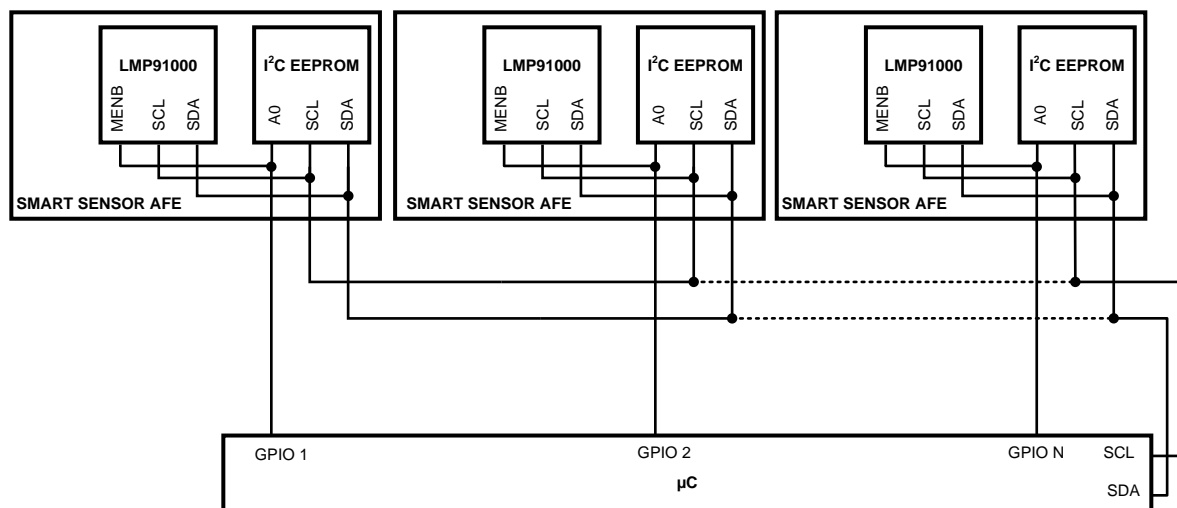


Figure 34. Smart Gas Sensor AFEs on I²C bus

POWER CONSUMPTION

The LMP91000 is intended for use in portable devices, so the power consumption is as low as possible in order to guarantee a long battery life. The total power consumption for the LMP91000 is below 10µA at 3.3v average over time, (this excludes any current drawn from any pin). A typical usage of the LMP91000 is in a portable gas detector and its power consumption is summarized in Table 3. This has the following assumptions:

- Power On only happens a few times over life, so its power consumption can be ignored.
- Deep Sleep mode is not used.
- The system is used about 8 hours a day, and 16 hours a day it is in Standby mode.
- Temperature Measurement is done about once per minute.

This results in an average power consumption of approximately 7.95 µA. This can potentially be further reduced, by using the Standby mode between gas measurements. It may even be possible, depending on the sensor used, to go into deep sleep for some time between measurements, further reducing the average power consumption.

Table 3. Power Consumption Scenario

	Deep Sleep	StandBy	3-Lead Amperometric Cell	Temperature Measurement TIA OFF	Temperature Measurement TIA ON	Total
Current consumption (µA) typical value	0.6	6.5	10	11.4	14.9	7.95
Time ON (%)	0	60	39	0	1	
Average (µA)	0	3.9	3.9	0	0.15	
Notes						
A1	OFF	ON	ON	ON	ON	
TIA	OFF	OFF	ON	OFF	ON	
TEMP SENSOR	OFF	OFF	OFF	ON	ON	
I²C interface	ON	ON	ON	ON	ON	

SENSOR TEST PROCEDURE

The LMP91000 has all the hardware and programmability features to implement some test procedures. The purpose of the test procedure is to:

- test proper function of the sensor (status of health)
- test proper connection of the sensor to the LMP91000

The test procedure is very easy. The variable bias block is user programmable through the digital interface. A step voltage can be applied by the end user to the positive input of A1. As a consequence a transient current will start flowing into the sensor (to charge its internal capacitance) and it will be detected by the TIA. If the current transient is not detected, either a sensor fault or a connection problem is present. The slope and the aspect of the transient response can also be used to detect sensor aging (for example, a cell that is drying and no longer efficiently conducts the current). After it is verified that the sensor is working properly, the LMP91000 needs to be reset to its original configuration. It is not required to observe the full transient in order to contain the testing time. All the needed information are included in the transient slopes (both edges). Figure 35 shows an example of the test procedure, a Carbon Monoxide sensor is connected to the LMP91000, two pulses are then sequentially applied to the bias voltage:

- from 0mV to 40mV
- from 40mV to -40mV

and finally the bias is set again at 0mV since this is the normal operation condition for this sensor.

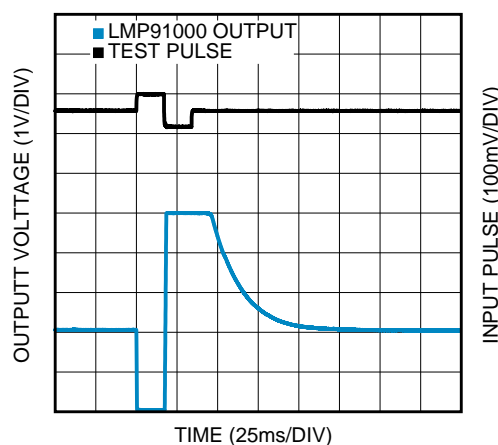


Figure 35. Test Procedure Example

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Top-Side Markings (4)	Samples
LMP91000SD/NOPB	ACTIVE	WSON	NHL	14	1000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	L91000	Samples
LMP91000SDE/NOPB	ACTIVE	WSON	NHL	14	250	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	L91000	Samples
LMP91000SDX/NOPB	ACTIVE	WSON	NHL	14	4500	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 85	L91000	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) Only one of markings shown within the brackets will appear on the physical device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMP91000SD/NOPB	WSO	NHL	14	1000	178.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LMP91000SDE/NOPB	WSO	NHL	14	250	178.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1
LMP91000SDX/NOPB	WSO	NHL	14	4500	330.0	12.4	4.3	4.3	1.3	8.0	12.0	Q1

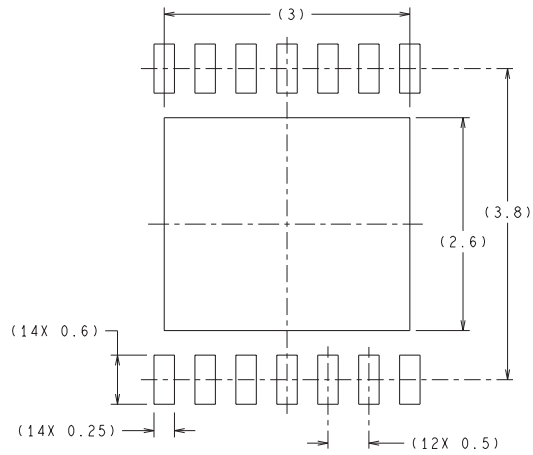
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

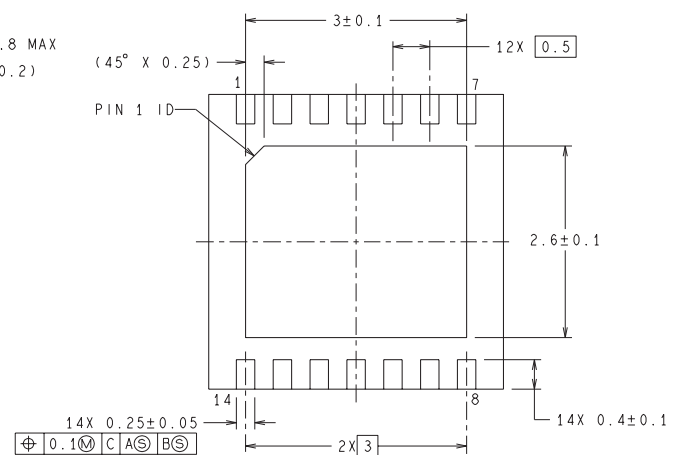
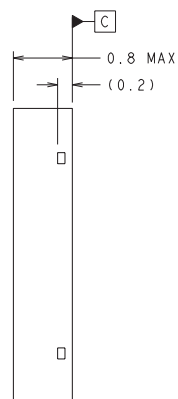
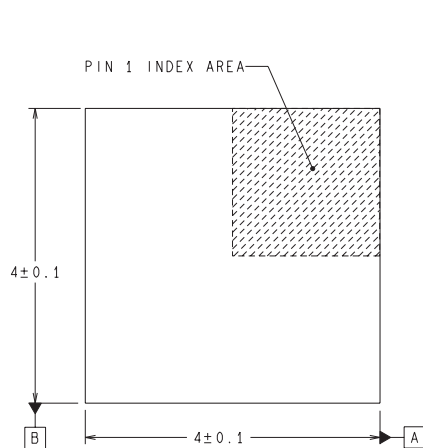
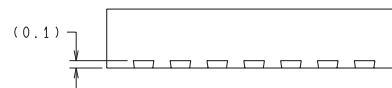
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMP91000SD/NOPB	WSON	NHL	14	1000	203.0	190.0	41.0
LMP91000SDE/NOPB	WSON	NHL	14	250	203.0	190.0	41.0
LMP91000SDX/NOPB	WSON	NHL	14	4500	358.0	343.0	63.0

NHL0014B



RECOMMENDED LAND PATTERN

DIMENSIONS ARE IN MILLIMETERS
DIMENSIONS IN () FOR REFERENCE ONLY



SDA14B (Rev A)

IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products

Audio	www.ti.com/audio
Amplifiers	amplifier.ti.com
Data Converters	dataconverter.ti.com
DLP® Products	www.dlp.com
DSP	dsp.ti.com
Clocks and Timers	www.ti.com/clocks
Interface	interface.ti.com
Logic	logic.ti.com
Power Mgmt	power.ti.com
Microcontrollers	microcontroller.ti.com
RFID	www.ti-rfid.com
OMAP Applications Processors	www.ti.com/omap
Wireless Connectivity	www.ti.com/wirelessconnectivity

Applications

Automotive and Transportation	www.ti.com/automotive
Communications and Telecom	www.ti.com/communications
Computers and Peripherals	www.ti.com/computers
Consumer Electronics	www.ti.com/consumer-apps
Energy and Lighting	www.ti.com/energy
Industrial	www.ti.com/industrial
Medical	www.ti.com/medical
Security	www.ti.com/security
Space, Avionics and Defense	www.ti.com/space-avionics-defense
Video and Imaging	www.ti.com/video

TI E2E Community

e2e.ti.com